

L Number	Hits	Search Text	DB	Time stamp
6	22	("6523555" "6535783" "6541401" "6556881" "6465263" "6230069" "6546508" "6291367" "6662355" "6625827" "672540	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 16:24
7	73	("0165636" "0017256" "0193899" "4957605" "5228280" "5240552" "5369545" "5342137" "5665214" "5695810" "578702	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 16:51
8	1	5270530.pn.	USPAT; US-PGPUB	2004/10/28 16:51
9	28	(("0165636" "0017256" "0193899" "4957605" "5228280" "5240552" "5369545" "5342137" "5665214" "5695810" "578702	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 17:17
10	19	and chamber\$4 ("5862054" "6074443" "6492281" "6618692" "6604012" "20010044667" "6560504" "6590179").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:06
13	8760	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 20:50
14	1766	118/719.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 20:50
15	358	427/9.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 20:50
16	2128	29/25.01.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 20:50
17	3004	700/19,49,52,99-104,108-111,119-121,123.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 21:08
18	7563	438/5-18.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
19	2045611	((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	

20	1413512	((process\$3 or cycle or defect\$4 or fail\$4 or fault\$4 or reject\$4) near3 (time or rate)) or ((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with (uniform\$3 or variability or capabilit\$4 or capacity))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 21:17
21	117771	((process\$3 or cycle or defect\$4 or fail\$4 or fault\$4 or reject\$4) near3 (time or rate)) or ((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) near3 (uniform\$3 or variability or capabilit\$4 or capacity))) with (perform\$4 or quality or qualification or qualify\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 21:19
22	2902	((process\$3 or cycle or defect\$4 or fail\$4 or fault\$4 or reject\$4) near3 (time or rate)) or ((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) near3 (uniform\$3 or variability or capabilit\$4 or capacity))) with (perform\$4 or quality or qualification or qualify\$3)) same chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 21:19
23	73	((process\$3 or cycle or defect\$4 or fail\$4 or fault\$4 or reject\$4) near3 (time or rate)) or ((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) near3 (uniform\$3 or variability or capabilit\$4 or capacity))).clm. with ((perform\$4 or quality or qualification or qualify\$3) with chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 21:59
24	14	((qualification or qualify\$3) with chamber).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:01
25	63	((qualification or qualify\$3) with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:04
26	10	((qualification or qualify\$3) with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5)).clm.) and (chamber with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:05
27	2168	((qualification or qualif\$5 or qual) with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5 or chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:05
28	894	((qualification or qualif\$5 or qual) near3 (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5 or chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:05
29	160	((qualification or qualif\$5 or qual) near3 (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5 or chamber))) and (chamber with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:06

30	44	(((qualification or qualif\$5 or qual) near3 (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5 or chamber))) and (chamber with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5))) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:06
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